











LMR16006Y-Q1

ZHCSDV3-JUNE 2015

LMR16006Y-Q1 具有高效率 ECO 模式的 SIMPLE SWITCHER® 器

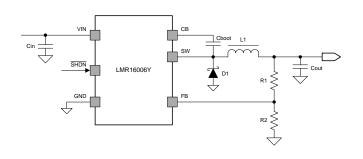
特性

- LMR16006Y-Q1 是一款汽车级产品,符合 AEC-Q100 1 级标准(运行结温范围为 -40°C 至
- 输入电压范围: 4V 至 40V, 瞬态电压最高达 65V
- 输出电流最高达 600mA
- 2.1MHz 开关频率
- ECO 模式下的超低待机电流为 28µA
- 1uA 关断电流
- 支持高占空比运行
- 可调节的 3.3V 和 5V 固定输出选项
- 内部补偿
- 高电压使能输入
- 内部软启动
- 过流保护
- 过热保护
- 小型总体解决方案尺寸(SOT-6L 封装)

应用范围

- 汽车
- 电池供电类设备
- 工业分布式电源系统
- 便携式手持仪器
- 便携式媒体播放器
- 汽车售后加装配件:视频、全球卫星定位系统 (GPS)、娱乐

简化电路原理图



3 说明

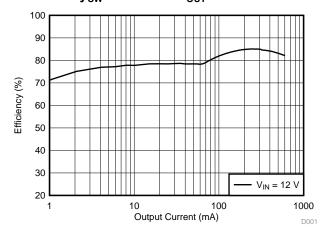
LMR16006Y-Q1 是一款脉宽调制 (PWM) DC-DC 降压 稳压器。 该器件广泛适用于从工业到汽车各类应用中 非稳压电源的电源调节。 该稳压器在 ECO 模式下的 待机电流为 28µA, 非常适合电池供电类系统。 该器件 具有 1µA 的超低关断电流,可进一步延长电池使用寿 命。 2.1MHz 的固定工作频率使得该器件在使用小型 外部组件的同时,仍能够保持较低的输出纹波电压。 该器件在内部实现了软启动和补偿电路,最大限度地减 少了与其搭配使用的外部组件数。 LMR16006Y-Q1 经 优化可提供高达 600mA 的负载电流, 其反馈电压典 型值为 0.765V。 该器件内置多种保护特性: 逐脉冲电 流限制保护、应对功耗过大的热感测和热关断保护。 LMR16006Y-Q1 采用薄型小外形尺寸晶体管 (SOT)-6L 封装 (2.9mm x 1.6mm)。

器件信息(1)

| HI II II IO | | | | | | | |
|-------------|---------|---------|--|--|--|--|--|
| 器件型号 | 封装 | 输出电压 | | | | | |
| LMR16006YQ | | 可调节 | | | | | |
| LMR16006YQ3 | SOT (6) | 固定 3.3V | | | | | |
| LMR16006YQ5 | | 固定 5V | | | | | |

(1) 要了解所有可用封装,请见数据表末尾的可订购产品附录。

效率与输出电流间的关系 $(f_{SW} = 2.1 MHz, V_{OUT} = 3.3 V)$







目录

| 1 | 特性 | | 8.3 Feature Description | 8 |
|---|--------------------------------------|----|--------------------------------|----|
| 2 | 应用范围 | | 8.4 Device Functional Modes | 9 |
| 3 | | 9 | Application and Implementation | 10 |
| 4 | 简化电路原理图1 | | 9.1 Application Information | 10 |
| 5 | 修订历史记录 | | 9.2 Typical Application | 10 |
| 6 | Pin Configuration and Functions | 10 | Power Supply Recommendations | 14 |
| 7 | Specifications 4 | 11 | Layout | 15 |
| • | 7.1 Absolute Maximum Ratings | | 11.1 Layout Guidelines | 15 |
| | 7.2 ESD Ratings | | 11.2 Layout Example | 15 |
| | 7.3 Recommended Operating Conditions | 12 | 器件和文档支持 | 16 |
| | 7.4 Thermal Information | | 12.1 相关文档 | 16 |
| | 7.5 Electrical Characteristics | | 12.2 社区资源 | 16 |
| | 7.6 Switching Characteristics | | 12.3 商标 | |
| | 7.7 Typical Characteristics | | 12.4 静电放电警告 | 16 |
| 8 | Detailed Description | | 12.5 术语表 | 16 |
| • | 8.1 Overview | 13 | 机械、封装和可订购信息 | 16 |
| | 8.2 Functional Block Diagram | | | |

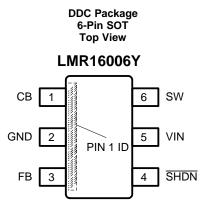
5 修订历史记录

| 日期 | 修订版本 | 注释 |
|------------|------|-------|
| 2015 年 6 月 | * | 首次发布。 |



www.ti.com.cn ZHCSDV3 – JUNE 2015

6 Pin Configuration and Functions



Pin Functions

| PIN | | 1/0 | DEGODIDATION | | | | |
|------|------------|-----|---|--|--|--|--|
| NAME | NUMBER I/O | | DESCRIPTION | | | | |
| СВ | 1 | I | Switch FET gate bias voltage. Connect C _{boot} capacitor between CB and SW. | | | | |
| GND | 2 | G | Ground connection. | | | | |
| FB | 3 | I | Feedback Input. Set feedback voltage divider ratio with V _{OUT} = V _{FB} (1 + (R1/R2)). | | | | |
| SHDN | 4 | I | Enable and disable input (high voltage tolerant). Internal pull-up current source. Pull below 1.25 V to disable. Float to enable. Establish input undervoltage lockout with two resistor divider. | | | | |
| VIN | 5 | I | Power input voltage pin. Input for internal supply and drain node input for internal high-side MOSFET. | | | | |
| SW | 6 | 0 | Switch node. Connect to inductor, diode, and C _{boot} capacitor. | | | | |

TEXAS INSTRUMENTS

7 Specifications

7.1 Absolute Maximum Ratings (1)

| | | MIN | MAX | UNIT |
|---|--------------------------------------|------|-----|------|
| | V _{IN} to GND | -0.3 | 65 | |
| Input voltages | SHDN to GND | -0.3 | 65 | |
| | FB to GND | -0.3 | 7 | ., |
| | CB to SW | -0.3 | 7 | V |
| Output voltages | SW to GND | -1 | 60 | |
| | SW to GND less than 30 ns transients | -2 | 60 | |
| T _J Operation junction temperature | | -40 | 150 | °C |
| Storage temperature, T _{stq} | | | 165 | °C |

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

| | | | VALUE | UNIT |
|--------------------|-------------------------|--|-------|------|
| V _(ESD) | | Human-body model (HBM), per AEC Q100-002 ⁽¹⁾ | ±2000 | V |
| | Electrostatic discharge | Electrostatic discharge Charged-device model (CDM), per AEC Q100-011 | ±500 | V |

⁽¹⁾ AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1)

| | | MIN | MAX | UNIT |
|----------------|--|------|-----|------|
| Buck regulator | V _{IN} | 4 | 40 | |
| | СВ | 4 | 46 | |
| | CB to SW | -0.3 | 6 | |
| | SW | -1 | 40 | V |
| | FB | 0 | 5.5 | |
| Control | SHDN | 0 | 40 | |
| Temperature | Operating junction temperature range, T _J | -40 | 125 | °C |

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.4 Thermal Information

over operating free-air temperature range (unless otherwise noted)

| | THERMAL METRIC (1) | LMR16006Y-Q1 | UNIT |
|--------------------|--|--------------|------|
| | | DDC (SOT) | |
| | | (6 PINS) | |
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance | 102 | |
| $R_{\theta JCtop}$ | Junction-to-case (top) thermal resistance | 36.9 | °C/W |
| $R_{\theta JB}$ | Junction-to board characterization parameter | 28.4 | |

All numbers apply for packages soldered directly onto a 3" x 3" PC board with 2 oz. copper on 4 layers in still air in accordance to JEDEC standards. Thermal resistance varies greatly with layout, copper thickness, number of layers in PCB, power distribution, number of thermal vias, board size, ambient temperature, and air flow.



www.ti.com.cn ZHCSDV3-JUNE 2015

7.5 Electrical Characteristics

Limits apply over the recommended operating junction temperature (T_J) range of -40°C to +125°C, unless otherwise stated. Minimum and Maximum limits are specified through test, design or statistical correlation. Typical values represent the most likely parametric norm at $T_J = 25$ °C, and are provided for reference purposes only. Unless otherwise specified, the following conditions apply: $V_{IN} = \overline{SHDN} = 12 \text{ V}.$

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|----------------------------------|---|---|-------|-------|-------|---------|
| V _{IN} (INPUT F | POWER SUPPLY) | | | | | |
| V _{IN} | Operating input voltage | | 4 | | 40 | V |
| I _{SHDN} | Shutdown supply current | V _{EN} = 0 V | | 1 | 3 | μΑ |
| IQ | Operating quiescent current (non- switching) | no load, V _{IN} = 12 V | | 28 | | μΑ |
| UVLO | Undervoltage lockout thresholds | Rising threshold | | | 4 | V |
| | | Falling threshold | 3 | | | V |
| SHDN | | • | | | • | |
| V _{SHDN_Thre} | Rising SHDN Threshold Voltage | | 1.05 | 1.25 | 1.38 | V |
| I _{SHDN} | Input current | SHDN = 2.3 V | | -4.2 | | |
| | | SHDN = 0.9 V | | -1 | | μA |
| I _{SHDN_HYS} | Hysteresis current | | | -3 | | μΑ |
| HIGH-SIDE I | MOSFET | | | | • | |
| R _{DS_ON} | On-resistance | V _{IN} = 12 V, CB to SW = 5.8 V | | 900 | | mΩ |
| VOLTAGE R | REFERENCE (FB PIN) | | | | | |
| V _{FB} | Feedback voltage | | 0.747 | 0.765 | 0.782 | V |
| V _{OUT} | Output voltage | Fixed 3.3 V output version | 3.201 | 3.3 | 3.399 | V |
| | | Fixed 5 V output version | 4.85 | 5 | 5.15 | V |
| CURRENT L | IMIT | | | | | |
| I _{LIMIT} | Peak current limit | V _{IN} = 12 V, T _J = 25°C | | 1200 | 1700 | mA |
| THERMAL F | PERFORMANCE | | | | | <u></u> |
| T _{SHDN} ⁽¹⁾ | Thermal shutdown threshold | | | 170 | | ٥C |
| T _{HYS} (1) | Hysteresis | | | 10 | | ٥С |
| | | | | | | |

⁽¹⁾ Ensured by design.

7.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-------------------------|----------------------|---------------------------|------|------|------|------|
| SW (SW PIN) | | | | | | |
| $f_{\sf SW}$ | Switching frequency | | 1785 | 2100 | 2415 | kHz |
| T _{ON_MIN} (1) | Minimum turn-on time | f _{SW} = 2.1 MHz | | 80 | | ns |
| D _{MAX} | Maximum duty cycle | | | 97% | | |

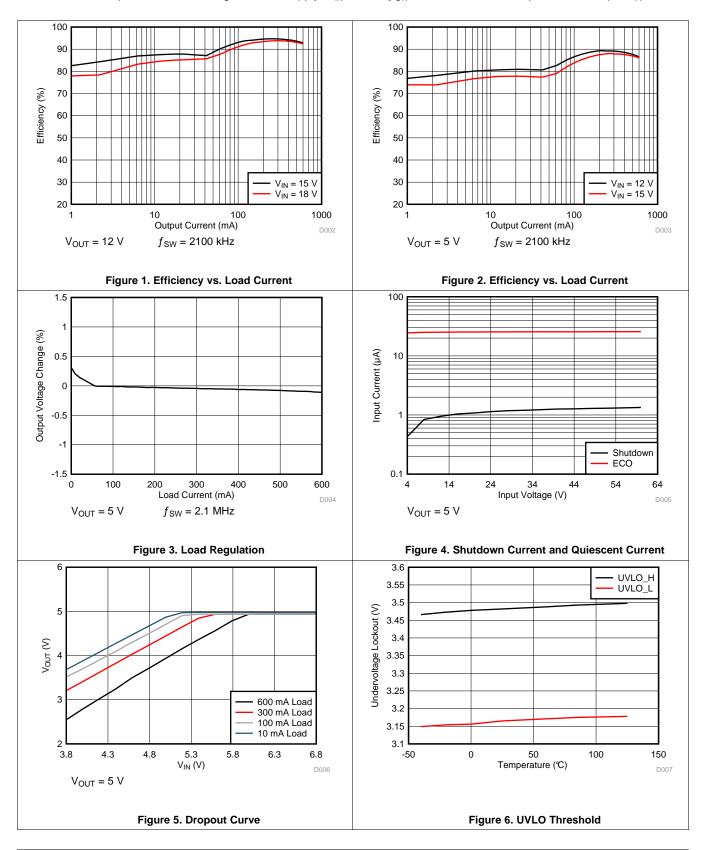
⁽¹⁾ Ensured by design.

ZHCSDV3 – JUNE 2015 www.ti.com.cn

TEXAS INSTRUMENTS

7.7 Typical Characteristics

Unless otherwise specified the following conditions apply: V_{IN} = 12 V, f_{SW} = 2100 kHz, L1 = 6.8 μ H, Cout = 10 μ F, T_A = 25°C.



www.ti.com.cn ZHCSDV3 – JUNE 2015

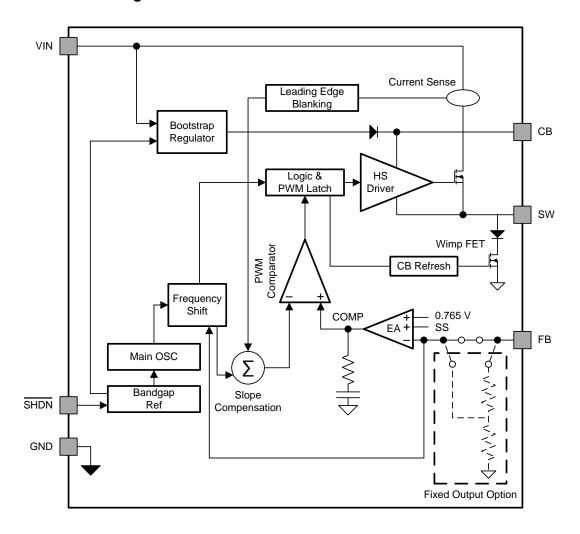
8 Detailed Description

8.1 Overview

The LMR16006Y-Q1 device is a 60 V, 600 mA, step-down (buck) regulator. The buck regulator has a very low quiescent current during light load to prolong battery life.

LMR16006Y-Q1 improves performance during line and load transients by implementing a constant frequency, current mode control which requires less output capacitance and simplifies frequency compensation design. The switching frequency is fixed at 2.1 MHz, thus smaller inductor and capacitor can be used. The device reduces the external component count by integrating the boot recharge diode. The bias voltage for the integrated high side MOSFET is supplied by a capacitor on the CB to SW pin. The boot capacitor voltage is monitored by an UVLO circuit and will turn the high side MOSFET off when the boot voltage falls below a preset threshold. The LMR16006Y-Q1 can operate at high duty cycles because of the boot UVLO and refresh the wimp FET. The output voltage can be stepped down to as low as the 0.8 V reference. Internal soft-start is featured to minimize inrush currents.

8.2 Functional Block Diagram



TEXAS INSTRUMENTS

8.3 Feature Description

8.3.1 Fixed Frequency PWM Control

The LMR16006Y-Q1 implements peak current mode control. The output voltage is compared through external resistors on the FB pin to an internal voltage reference by an error amplifier which drives the internal COMP node. An internal oscillator initiates the turn on of the high side power switch. The error amplifier output is compared to the high side power switch current. When the power switch current reaches the level set by the internal COMP voltage, the power switch is turned off. The internal COMP node voltage will increase and decrease as the output current increases and decreases. The device implements a current limit by clamping the COMP node voltage to a maximum level.

8.3.2 Bootstrap Voltage (CB)

The LMR16006Y-Q1 has an integrated boot regulator, and requires a small ceramic capacitor between the CB and SW pins to provide the gate drive voltage for the high side MOSFET. The CB capacitor is refreshed when the high side MOSFET is off and the low side diode conducts. To improve drop out, the LMR16006Y-Q1 is designed to operate at 97% duty cycle as long as the CB to SW pin voltage is greater than 3 V. When the voltage from CB to SW drops below 3 V, the high side MOSFET is turned off using an UVLO circuit which allows the low side diode to conduct and refresh the charge on the CB capacitor. Since the supply current sourced from the CB capacitor is low, the high side MOSFET can remain on for more switching cycles than are required to refresh the capacitor, thus the effective duty cycle of the switching regulator is high. Attention must be taken in maximum duty cycle applications with light load. To ensure SW can be pulled to ground to refresh the CB capacitor, an internal circuit will charge the CB capacitor when the load is light or the device is working in dropout condition.

8.3.3 Output Voltage Setting

The output voltage is set using the feedback pin and a resistor divider connected to the output as shown on the front page schematic. The feedback pin voltage 0.765 V, so the ratio of the feedback resistors sets the output voltage according to the following equation: $V_{OUT} = 0.765 \text{ V} (1 + (R1/R2))$. Typically R2 will be given as 1 k Ω to 100 k Ω for a starting value. To solve for R1 given R2 and V_{OUT} use R1 = R2 (($V_{OUT}/0.765 \text{ V}) - 1$).

8.3.4 Enable SHDN and VIN Undervoltage Lockout

LMR16006Y-Q1 \overline{SHDN} pin is a high voltage tolerant input with an internal pull up circuit. The device can be enabled even if the \overline{SHDN} pin is floating. The regulator can also be turned on using 1.23 V or higher logic signals. If the use of a higher voltage is desired due to system or other constraints, a 100 k Ω or larger resistor is recommended between the applied voltage and the \overline{SHDN} pin to protect the device. When \overline{SHDN} is pulled down to 0 V, the chip is turned off and enters the lowest shutdown current mode. In shutdown mode the supply current will be decreased to approximately 1 μ A. If the shutdown function is not to be used the \overline{SHDN} pin may be tied to V_{IN} via 100 k Ω resistor. The maximum voltage to the \overline{SHDN} pin should not exceed 60 V. LMR16006Y-Q1 has an internal UVLO circuit to shutdown the output if the input voltage falls below an internally fixed UVLO threshold level. This ensures that the regulator is not latched into an unknown state during low input voltage conditions. The regulator will power \underline{up} when the input voltage exceeds the voltage level. If there is a requirement for a higher UVLO voltage, the \overline{SHDN} can be used to adjust the system UVLO by using external resistors.

8.3.5 Current Limit

The LMR16006Y-Q1 implements current mode control which uses the internal COMP voltage to turn off the high side MOSFET on a cycle-by-cycle basis. Each cycle the switch current and internal COMP voltage are compared, when the peak switch current intersects the COMP voltage, the high side switch is turned off. During overcurrent conditions that pull the output voltage low, the error amplifier will respond by driving the COMP node high, increasing the switch current. The error amplifier output is clamped internally, which functions as a switch current limit.



ZHCSDV3-JUNE 2015 www.ti.com.cn

Feature Description (continued)

8.3.6 Overvoltage Transient Protection

The LMR16006Y-Q1 incorporates an overvoltage transient protection (OVTP) circuit to minimize voltage overshoot when recovering from output fault conditions or strong unload transients on power supply designs with low value output capacitance. For example, when the power supply output is overloaded the error amplifier compares the actual output voltage to the internal reference voltage. If the FB pin voltage is lower than the internal reference voltage for a considerable time, the output of the error amplifier will respond by clamping the error amplifier output to a high voltage. Thus, requesting the maximum output current. Once the condition is removed, the regulator output rises and the error amplifier output transitions to the steady state duty cycle. In some applications, the power supply output voltage can respond faster than the error amplifier output can respond, this actuality leads to the possibility of an output overshoot. The OVTP feature minimizes the output overshoot, when using a low value output capacitor, by implementing a circuit to compare the FB pin voltage to OVTP threshold which is 108% of the internal voltage reference. If the FB pin voltage is greater than the OVTP threshold, the high side MOSFET is disabled preventing current from flowing to the output and minimizing output overshoot. When the FB voltage drops lower than the OVTP threshold, the high side MOSFET is allowed to turn on at the next clock cycle.

8.3.7 Thermal Shutdown

The device implements an internal thermal shutdown to protect itself if the junction temperature exceeds 170°C(typ). The thermal shutdown forces the device to stop switching when the junction temperature exceeds the thermal trip threshold. Once the junction temperature decreases below 160°C(typ), the device reinitiates the power up sequence.

8.4 Device Functional Modes

8.4.1 Continuous Conduction Mode

The LMR16006Y-Q1 steps the input voltage down to a lower output voltage. In continuous conduction mode (when the inductor current never reaches zero at CCM), the buck regulator operates in two cycles. The power switch is connected between V_{IN} and SW. In the first cycle of operation the transistor is closed and the diode is reverse biased. Energy is collected in the inductor and the load current is supplied by Cout and the rising current through the inductor. During the second cycle the transistor is open and the diode is forward biased due to the fact that the inductor current cannot instantaneously change direction. The energy stored in the inductor is transferred to the load and output capacitor. The ratio of these two cycles determines the output voltage. The output voltage is defined approximately as: $D = V_{OLIT}/V_{IN}$ and D' = (1-D) where D is the duty cycle of the switch, D and D' will be required for design calculations.

8.4.2 **ECO Mode**

The LMR16006Y-Q1 operates in ECO mode at light load currents to improve efficiency by reducing switching and gate drive losses. The LMR16006Y-Q1 is designed so that if the output voltage is within regulation and the peak switch current at the end of any switching cycle is below the sleep current threshold, I_{INDUCTOR} ≤ 80 mA, the device enters ECO mode. For ECO mode operation, the LMR16006Y-Q1 senses peak current, not average or load current, so the load current where the device enters ECO mode is dependent on VIN, VOUT and the output inductor value. When the load current is low and the output voltage is within regulation, the device enters an ECO mode and draws only 28 µA input guiescent current.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LMR16006Y-Q1 is a step down DC-to-DC regulator. It is typically used to convert a higher DC voltage to a lower DC voltage with a maximum output current of 600 mA. *Detailed Design Procedure* can be used to select components for the LMR16006Y-Q1.

9.2 Typical Application

Figure 7 shows typical application where user can adjust output by R1 and R2.

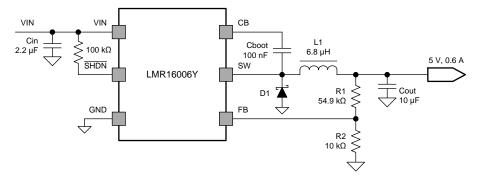


Figure 7. Application Circuit, 5 V Output

9.2.1 Design Requirements

Example requirements for typical buck regulators with high-efficiency applications:

Table 1. Design Requirements

| DESIGN PARA | METER | EXAMPLE VALUE | |
|------------------------------|--------------------------------|---------------------------|--|
| Input voltage | e, V _{IN} | 9 V to 16 V, typical 12 V | |
| Output voltage | e, V _{OUT} | 5 V ± 3% | |
| Maximum output cu | ırrent I _{O_max} | 0.6 A | |
| Minimum output cu | rent I _{O_min} 0.03 A | | |
| Transient response 0 | .03 A to 0.6 A | 5% | |
| Output voltage | e ripple | 1% | |
| Switching freque | ency f_{SW} | 2.1 MHz | |
| Torget during Lond Transient | Overvoltage peak value | 106% of output voltage | |
| Target during Load Transient | Undervoltage value | 91% of output voltage | |

9.2.2 Detailed Design Procedure

This example details the design of a high frequency switching regulator using ceramic output capacitors. A few parameters must be known in order to start the design process. These parameters are typically determined at the system level:



ZHCSDV3-JUNE 2015 www.ti.com.cn

9.2.2.1 Output Inductor Selection

The most critical parameters for the inductor are the inductance, peak current and the DC resistance. The inductance is related to the peak-to-peak inductor ripple current, the input and the output voltages. Since the ripple current increases with the input voltage, the maximum input voltage is always used to determine the inductance. To calculate the minimum value of the output inductor, use Equation 1. KIND is a coefficient that represents the amount of inductor ripple current relative to the maximum output current. A reasonable value is setting the ripple current to be 30%-40% of the DC output current. For this design example, the minimum inductor value is calculated to be 6.82 µH, and a nearest standard value was chosen: 6.8 µH. For the output filter inductor, it is important that the RMS current and saturation current ratings not be exceeded. The RMS and peak inductor current can be found from Equation 3 and Equation 4. The inductor ripple current is 0.074 A, and the RMS current is 0.60 A. As the equation set demonstrates, lower ripple currents will reduce the output voltage ripple of the regulator but will require a larger value of inductance. A good starting point for most applications is 6.8 µH with a 1.6 A current rating. Using a rating near 1.6 A will enable the LMR16006Y-Q1 to current limit without saturating the inductor. This is preferable to the LMR16006Y-Q1 going into thermal shutdown mode and the possibility of damaging the inductor if the output is shorted to ground or other long-term overload.

$$L_{o\,\text{min}} = \frac{V_{in\,\text{max}} - V_{out}}{I_o \times K_{IND}} \times \frac{V_{out}}{V_{in\,\text{max}} \times f_{sw}} \tag{1}$$

$$I_{ripple} = \frac{V_{out} \times (V_{in \max} - V_{out})}{V_{in \max} \times L_o \times f_{sw}}$$

$$I_{L-RMS} = \sqrt{I_o^2 + \frac{1}{12} I_{ripple}^2}$$
(2)

$$I_{L-RMS} = \sqrt{I_o^2 + \frac{1}{12}I_{ripple}^2}$$
 (3)

$$I_{L-peak} = I_o + \frac{I_{ripple}}{2} \tag{4}$$

9.2.2.2 Output Capacitor Selection

The selection of Cout is mainly driven by three primary considerations. The output capacitor will determine the modulator pole, the output voltage ripple, and how the regulator responds to a large change in load current. The output capacitance needs to be selected based on the most stringent of these three criteria.

The desired response to a large change in the load current is the first criteria. The regulator usually needs two or more clock cycles for the control loop to see the change in load current and output voltage and adjust the duty cycle to react to the change. The output capacitance must be large enough to supply the difference in current for 2 clock cycles while only allowing a tolerable amount of droop in the output voltage. Equation 5 shows the minimum output capacitance necessary to accomplish this. The transient load response is specified as a 3% change in V_{OUT} for a load step from 0.03 A to 0.6 A (full load), $\Delta I_{OUT} = 0.6 - 0.03 = 0.57$ A and $\Delta V_{OUT} = 0.03 \times 5$ = 0.15 V. Using these numbers gives a minimum capacitance of 3.62 µF. For ceramic capacitors, the ESR is usually small enough to ignore in this calculation. Aluminum electrolytic and tantalum capacitors have higher ESR that should be taken into account.

The stored energy in the inductor will produce an output voltage overshoot when the load current rapidly decreases. The output capacitor must also be sized to absorb energy stored in the inductor when transitioning from a high load current to a lower load current. Equation 6 is used to calculate the minimum capacitance to keep the output voltage overshoot to a desired value. Where L is the value of the inductor, IOH is the output current under heavy load, IOL is the output under light load, Vf is the final peak output voltage, and Vi is the initial capacitor voltage. For this example, the worst case load step will be from 0.6 A to 0.03 A. The output voltage will increase during this load transition and the stated maximum in our specification is 3% of the output voltage. This will make $Vo_{overshoot} = 1.03 \times 5 = 5.15 \text{ V}$. V_{i} is the initial capacitor voltage which is the nominal output voltage of 5 V. Using these numbers in Equation 6 yields a minimum capacitance of 1.6 µF.

Equation 7 calculates the minimum output capacitance needed to meet the output voltage ripple specification. Where f_{sw} is the switching frequency, V_{o_ripple} is the maximum allowable output voltage ripple, and I_{L_ripple} is the inductor ripple current. Equation 7 yields 95 nF.

Equation 8 calculates the maximum ESR an output capacitor can have to meet the output voltage ripple specification. Equation 8 indicates the ESR should be less than 623 m Ω .



(7)

Additional capacitance de-ratings for aging, temperature and dc bias should be factored in which will increase this minimum value. For this example, 10 μ F ceramic capacitors will be used. Capacitors in the range of 4.7 μ F-100 μ F are a good starting point with an ESR of 0.7 Ω or less.

$$C_{out} > \frac{2 \times \Delta I_{out}}{fsw \times \Delta V_{out}} \tag{5}$$

$$C_{out} > L_o \times \frac{(Ioh^2 - Iol^2)}{(Vf^2 - Vi^2)} \tag{6}$$

$$C_{out} > \frac{1}{8 \times fsw} \times \frac{1}{\frac{V_{o_ripple}}{I_{L_ripple}}}$$

$$R_{ESR} < \frac{V_{o_ripple}}{I_{L_ripple}} \tag{8}$$

9.2.2.3 Schottky Diode Selection

The breakdown voltage rating of the diode is preferred to be 25% higher than the maximum input voltage. In the target application, the current rating for the diode should be equal or greater to the maximum output current for best reliability in most applications. In cases where the input voltage is not much greater than the output voltage the average diode current is lower. In this case it is possible to use a diode with a lower average current rating, approximately $(1-D) \times I_{OUT}$. However the peak current rating should be higher than the maximum load current. A 0.5 A to 1 A rated diode is a good starting point.

9.2.2.4 Input Capacitor Selection

A low ESR ceramic capacitor is needed between the VIN pin and ground pin. This capacitor prevents large switching voltage transients from appearing at the input. Use a 1 μ F-10 μ F value with X5R or X7R dielectric. Depending on construction, a ceramic capacitor's value can decrease up to 50% of its nominal value when rated voltage is applied. Consult with the capacitor manufactures data sheet for information on capacitor derating over voltage and temperature. The capacitor must also have a ripple current rating greater than the maximum input current ripple of the LMR16006Y-Q1. The input ripple current can be calculated using below Equation 9.

For this example design, one 2.2 μ F, 50 V capacitor is selected. The input capacitance value determines the input ripple voltage of the regulator. The input voltage ripple can be calculated using Equation 10. Using the design example values, $I_{OUT_max} = 0.6$ A, Cin = 2.2 μ F, $f_{SW} = 2100$ kHz, yields an input voltage ripple of 33 mV and a rms input ripple current of 0.3 A.

$$I_{cirms} = I_{out} \times \sqrt{\frac{V_{out}}{V_{in\,\text{min}}} \times \frac{(V_{in\,\text{min}} - V_{out})}{V_{in\,\text{min}}}}$$
(9)

$$\Delta V_{in} = \frac{I_{out \, \text{max}} \times 0.25}{C_{in} \times fsw} \tag{10}$$

9.2.2.5 Bootstrap Capacitor Selection

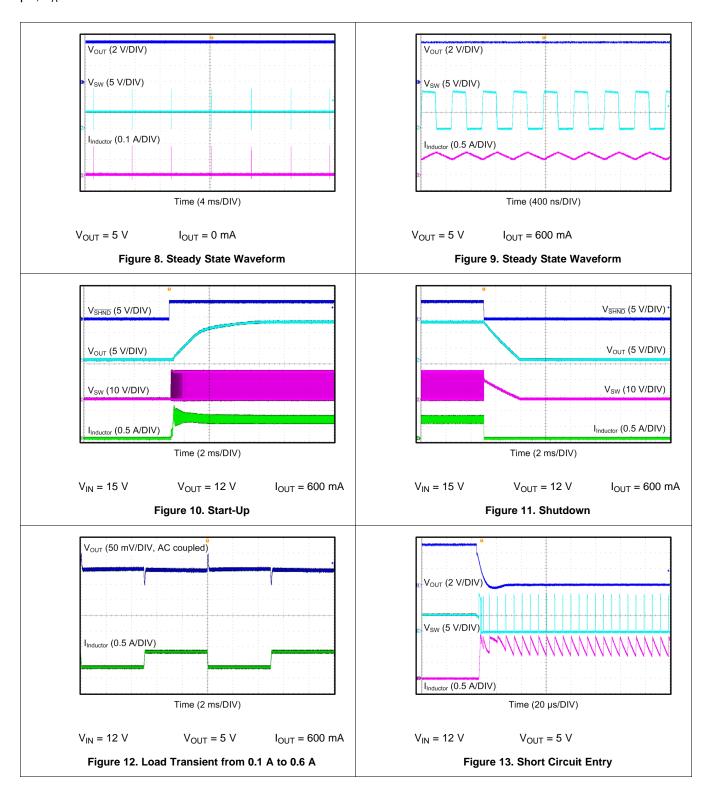
A 0.1 μF ceramic capacitor or larger is recommended for the bootstrap capacitor (C_{BOOT}). For applications where the input voltage is close to output voltage a larger capacitor is recommended, generally 0.1 μF to 1 μF to ensure plenty of gate drive for the internal switches and a consistently low R_{DSON} . A ceramic capacitor with an X7R or X5R grade dielectric with a voltage rating of 10 V or higher is recommended because of the stable characteristics over temperature and voltage.



www.ti.com.cn

9.2.3 Application Curves

Unless otherwise specified the following conditions apply: V_{IN} = 12 V, f_{SW} = 2100 kHz, L1 = 6.8 μ H, C_{OUT} = 10 μ F, T_A = 25°C.



ZHCSDV3 – JUNE 2015 www.ti.com.cn

TEXAS INSTRUMENTS

9.2.4 Additional Application Circuit

Figure 14 shows the typical application circuit with a fixed output.

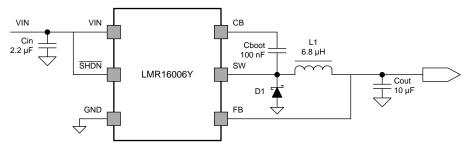


Figure 14. LMR16006Y-Q1 Application Circuit, Fixed Output

10 Power Supply Recommendations

The LMR16006Y-Q1 is designed to operate from an input voltage supply range between 4 V and 60 V. This input supply should be able to withstand the maximum input current and maintain a voltage above 4 V. The resistance of the input supply rail should be low enough that an input current transient does not cause a high enough drop at the LMR16006Y-Q1 supply voltage that can cause a false UVLO fault triggering and system reset. If the input supply is located more than a few inches from the LMR16006Y-Q1, additional bulk capacitance may be required in addition to the ceramic input capacitors.

www.ti.com.cn

Layout

11.1 Layout Guidelines

Layout is a critical portion of good power supply design. The following guidelines will help users design a PCB with the best power conversion performance, thermal performance, and minimized generation of unwanted EMI.

- 1. The feedback network, resistors R1 and R2, should be kept close to the FB pin, and away from the inductor to minimize coupling noise into the feedback pin.
- 2. The input bypass capacitor Cin must be placed close to the V_{IN} pin. This will reduce copper trace resistance which effects input voltage ripple of the IC.
- 3. The inductor L1 should be placed close to the SW pin to reduce magnetic and electrostatic noise.
- 4. The output capacitor, Cout should be placed close to the junction of L1 and the diode D1. The L1, D1, and Cout trace should be as short as possible to reduce conducted and radiated noise and increase overall efficiency.
- 5. The ground connection for the diode, Cin, and Cout should be as small as possible and tied to the system ground plane in only one spot (preferably at the Cout ground point) to minimize conducted noise in the system ground plane.
- 6. For more detail on switching power supply layout considerations see AN-1149 Layout Guidelines for Switching Power Supplies SNVA021

11.2 Layout Example

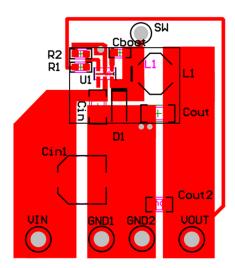


Figure 15. Layout

TEXAS INSTRUMENTS

12 器件和文档支持

12.1 相关文档

AN-1149《开关电源布局指南》 (文献编号: SNVA021)。

12.2 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 商标

E2E is a trademark of Texas Instruments.

SIMPLE SWITCHER is a registered trademark of TI.

All other trademarks are the property of their respective owners.

12.4 静电放电警告



这些装置包含有限的内置 ESD 保护。 存储或装卸时,应将导线一起截短或将装置放置于导电泡棉中,以防止 MOS 门极遭受静电损伤。

12.5 术语表

SLYZ022 — TI 术语表。

这份术语表列出并解释术语、首字母缩略词和定义。

13 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不 对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本,请查阅左侧的导航栏。





10-Dec-2020

PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan | Lead finish/ Ball material | MSL Peak Temp | Op Temp (°C) | Device Marking (4/5) | Samples |
|-------------------|------------|--------------|--------------------|------|----------------|--------------|-------------------------------|--------------------|--------------|----------------------|---------|
| LMR16006YQ3DDCRQ1 | ACTIVE | SOT-23-THIN | DDC | 6 | 3000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | Q32Y | Samples |
| LMR16006YQ3DDCTQ1 | ACTIVE | SOT-23-THIN | DDC | 6 | 250 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | Q32Y | Samples |
| LMR16006YQ5DDCRQ1 | ACTIVE | SOT-23-THIN | DDC | 6 | 3000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | Q52Y | Samples |
| LMR16006YQ5DDCTQ1 | ACTIVE | SOT-23-THIN | DDC | 6 | 250 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | Q52Y | Samples |
| LMR16006YQDDCRQ1 | ACTIVE | SOT-23-THIN | DDC | 6 | 3000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | Q02Y | Samples |
| LMR16006YQDDCTQ1 | ACTIVE | SOT-23-THIN | DDC | 6 | 250 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | Q02Y | Samples |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



PACKAGE OPTION ADDENDUM

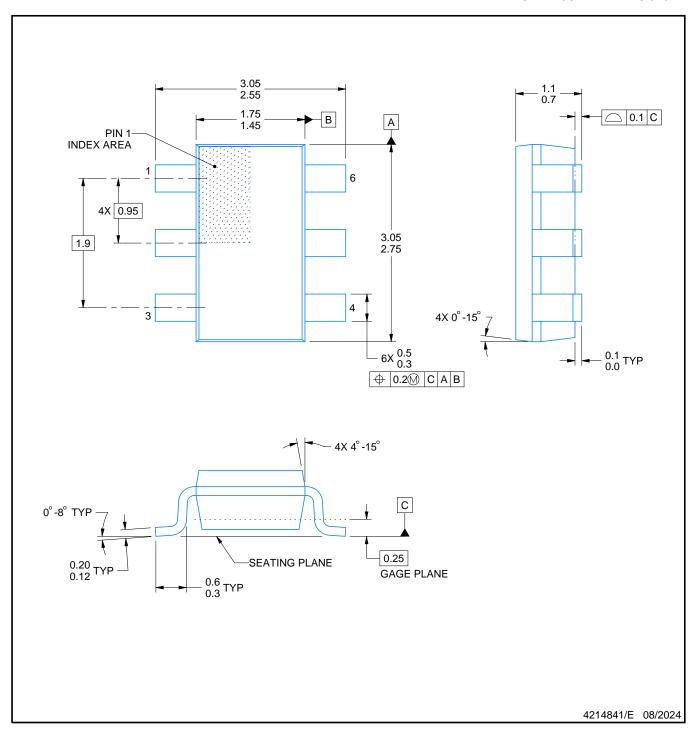
10-Dec-2020

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



SMALL OUTLINE TRANSISTOR

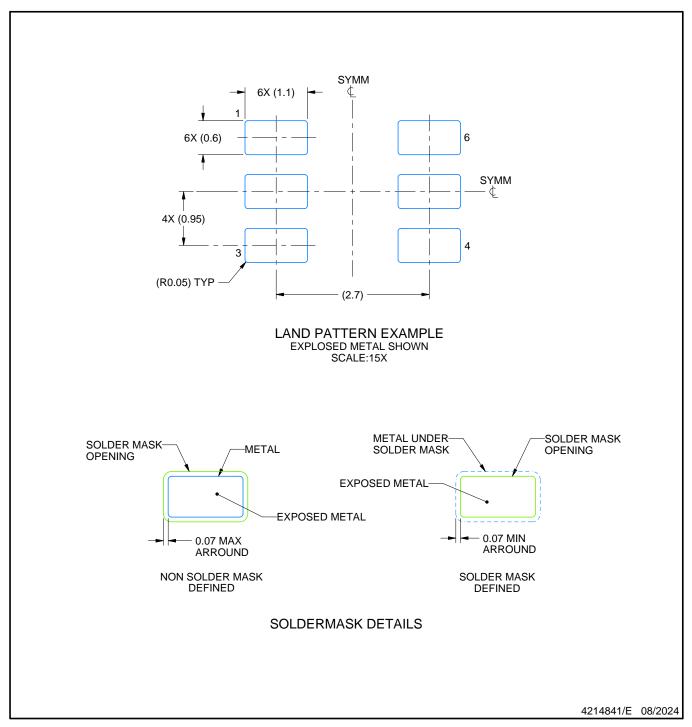


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC MO-193.



SMALL OUTLINE TRANSISTOR

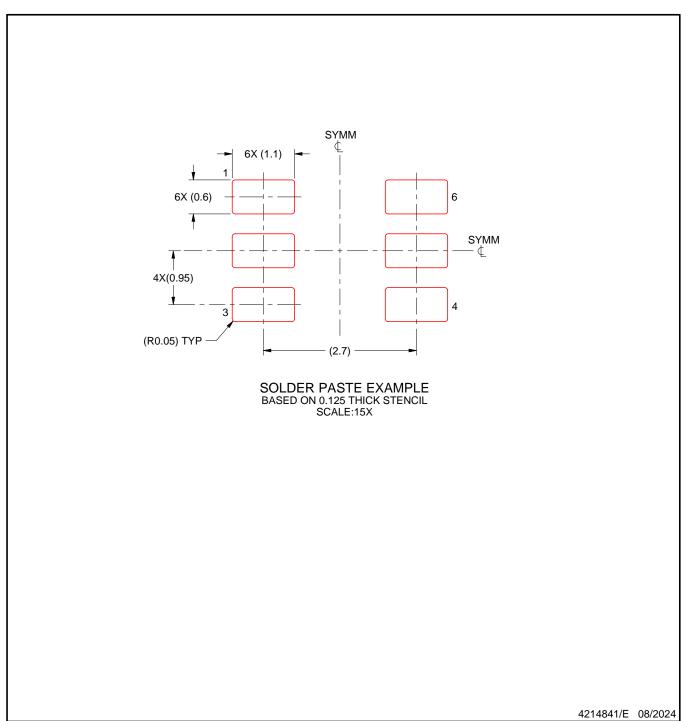


NOTES: (continued)

- 4. Publication IPC-7351 may have alternate designs.
- 5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

 7. Board assembly site may have different recommendations for stencil design.



重要声明和免责声明

TI"按原样"提供技术和可靠性数据(包括数据表)、设计资源(包括参考设计)、应用或其他设计建议、网络工具、安全信息和其他资源,不保证没有瑕疵且不做出任何明示或暗示的担保,包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任:(1) 针对您的应用选择合适的 TI 产品,(2) 设计、验证并测试您的应用,(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更,恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务,TI 对此概不负责。

TI 提供的产品受 TI 的销售条款或 ti.com 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2024,德州仪器 (TI) 公司